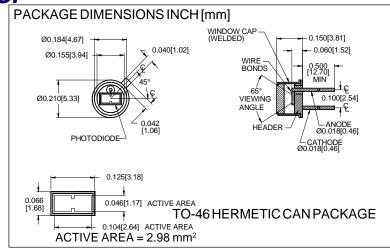
PHOTONIC Silicon Photodiode, Blue Enhanced **Photoconductive** Type PDB-C104 DETECTORS INC.





FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The PDB-C104 is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a flat window.

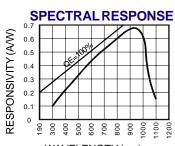
APPLICATIONS

- Instrumentation
- Character recognition
- Laser detection
- Fiber optic

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V_{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature	-55	+150	∘C	
T _o	Operating Temperature Range	-40	+125	∘C	
T _s	Soldering Temperature*		+240	∘C	
I _L	Light Current		0.5	mA	

^{*1/16} inch from case for 3 secs max



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS		
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	40	45		μ A		
I _D	Dark Current	H = 0, V _R = 10 V		.15	1.0	nA		
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$.5	1.0		GΩ		
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/°C		
C _J	Junction Capacitance	H = 0, V _R = 10 V**		10		pF		
λrange	Spectral Application Range	Spot Scan	350		1100	nm		
λр	Spectral Response - Peak	Spot Scan		950		nm		
V _{BR}	Breakdown Voltage	I = 10 μA	70	100		V		
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹⁴		W/ √Hz		
tr	Response Time	$RL = 1 K\Omega V_p = 50 V$		10		nS		